



STN1N20

N - CHANNEL 200V - 1.2 Ω - 1A - SOT-223 POWER MOS TRANSISTOR

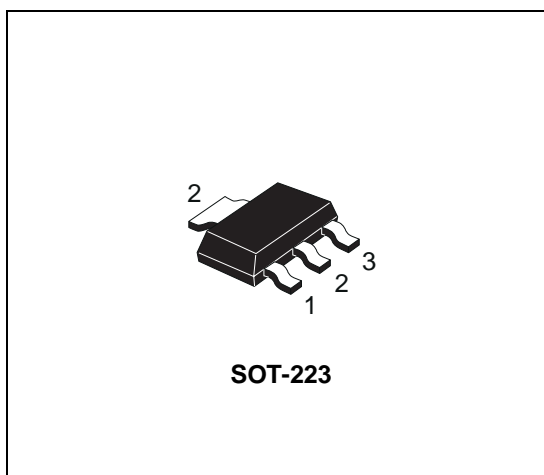
PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _{DCONT}
STN1N20	200 V	< 1.5 Ω	1 A

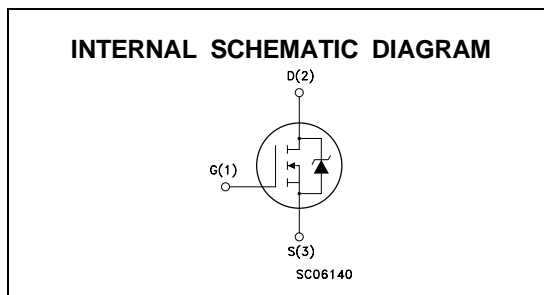
- TYPICAL R_{DS(on)} = 1.2 Ω
- AVALANCHE RUGGED TECHNOLOGY
- SOT-223 CAN BE WAVE OR REFLOW SOLDERED
- AVAILABLE IN TAPE AND REEL ON REQUEST
- 150 °C OPERATING TEMPERATURE
- APPLICATION ORIENTED CHARACTERIZATION

APPLICATIONS

- HARD DISK DRIVERS
- SMALL MOTOR CURRENT SENSE CIRCUITS
- DC-DC CONVERTERS AND POWER SUPPLIES



SOT-223



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	200	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 k Ω)	200	V
V _{GS}	Gate-source Voltage	± 20	V
I _D (*)	Drain Current (continuous) at T _c = 25 °C	1	A
I _D (*)	Drain Current (continuous) at T _c = 100 °C	0.6	A
I _{DM} (•)	Drain Current (pulsed)	4	A
P _{tot}	Total Dissipation at T _c = 25 °C	2.9	W
	Derating Factor	0.023	W/°C
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

(*) Limited by package

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THERMAL DATA

$R_{thj-pcb}$	Thermal Resistance Junction-PC Board	Max	43	$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal Resistance Junction-ambient (Surface Mounted)	Max	60	$^{\circ}\text{C}/\text{W}$
T_I	Maximum Lead Temperature For Soldering Purpose		260	$^{\circ}\text{C}$

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	1	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 25\text{ V}$)	10	mJ

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\ \mu\text{A}$ $V_{GS} = 0$	200			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_c = 125^{\circ}\text{C}$			10 100	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\ \mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\text{ V}$ $I_D = 0.5\text{ A}$		1.2	1.5	Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10\text{ V}$	1			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 0.5\text{ A}$	0.3	0.7		S
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}$ $f = 1\text{ MHz}$ $V_{GS} = 0\text{ V}$		290	400	pF
C_{oss}	Output Capacitance			50	70	pF
C_{rss}	Reverse Transfer Capacitance			10	15	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 100\text{ V}$ $I_D = 2\text{ A}$		7	10	ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		6	10	ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 160\text{ V}$ $I_D = 4\text{ A}$ $R_G = 47\ \Omega$ $V_{GS} = 10\text{ V}$		270		A/ μ s
Q_g	Total Gate Charge	$V_{DD} = 160\text{ V}$ $I_D = 4\text{ A}$ $V_{GS} = 10\text{ V}$		13	20	nC
Q_{gs}	Gate-Source Charge			7		nC
Q_{gd}	Gate-Drain Charge			4		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 160\text{ V}$ $I_D = 4\text{ A}$		6	10	ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		5	10	ns
t_c	Cross-over Time			13	20	ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				1	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				4	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 1\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 4\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		170		ns
Q_{rr}	Reverse Recovery Charge			1		μ C
I_{RRM}	Reverse Recovery Current			12		A

(*) Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

Fig. 1: Unclamped Inductive Load Test Circuit

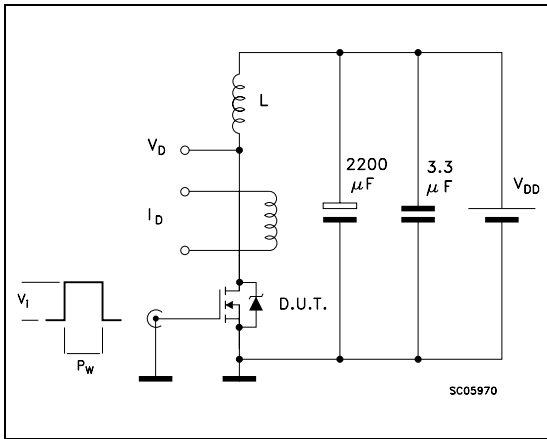


Fig. 2: Unclamped Inductive Waveform

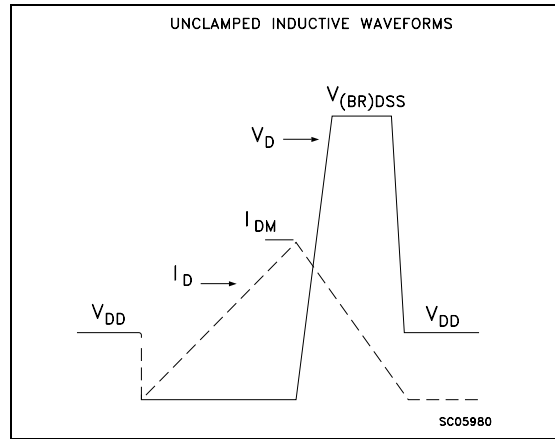


Fig. 3: Switching Times Test Circuits For Resistive Load

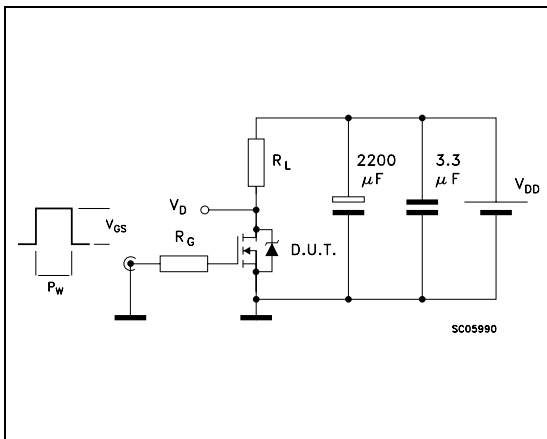


Fig. 4: Gate Charge test Circuit

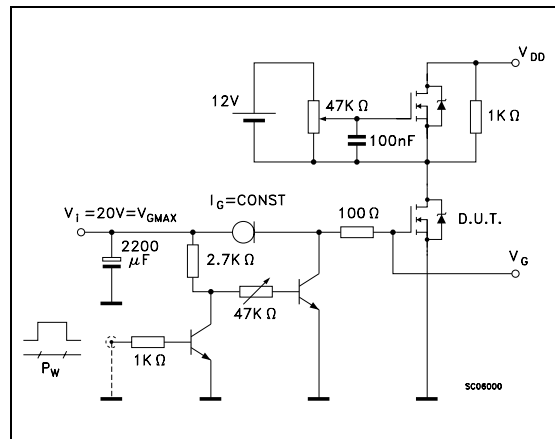
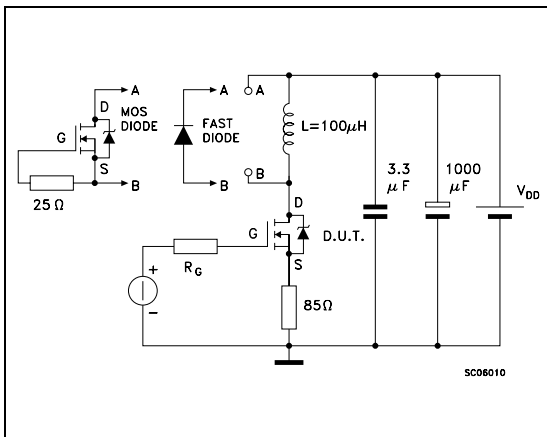
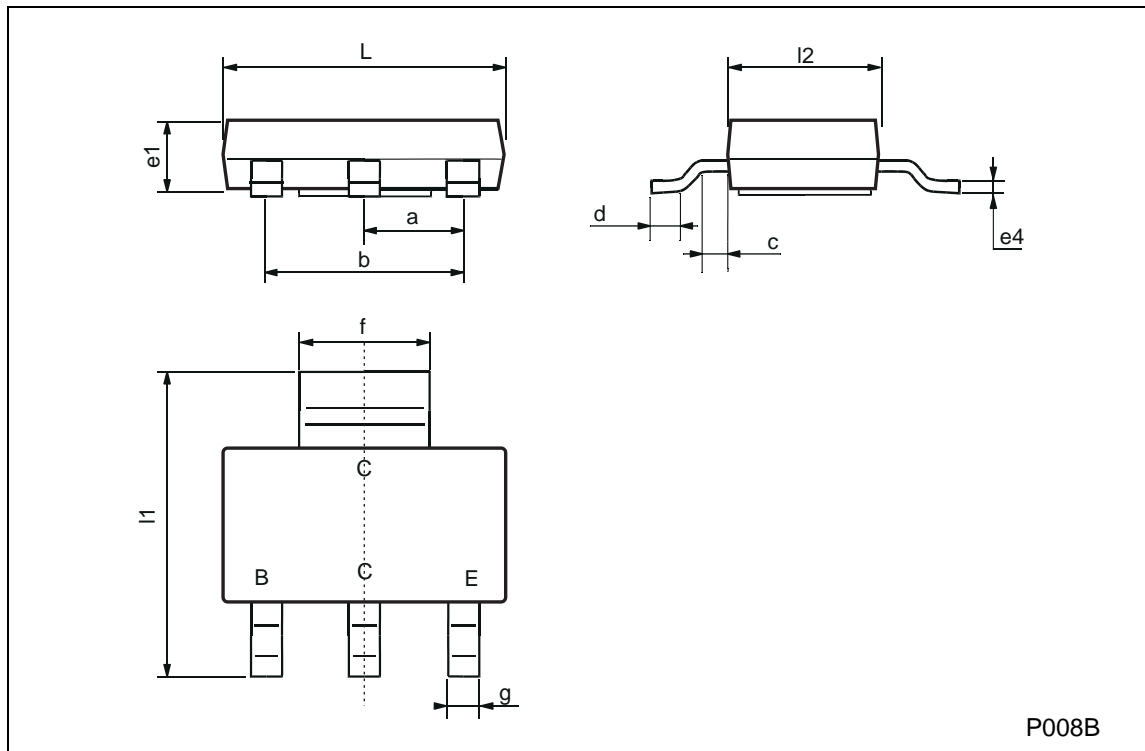


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



SOT-223 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a	2.27	2.3	2.33	89.4	90.6	91.7
b	4.57	4.6	4.63	179.9	181.1	182.3
c	0.2	0.4	0.6	7.9	15.7	23.6
d	0.63	0.65	0.67	24.8	25.6	26.4
e1	1.5	1.6	1.7	59.1	63	66.9
e4			0.32			12.6
f	2.9	3	3.1	114.2	118.1	122.1
g	0.67	0.7	0.73	26.4	27.6	28.7
l1	6.7	7	7.3	263.8	275.6	287.4
l2	3.5	3.5	3.7	137.8	137.8	145.7
L	6.3	6.5	6.7	248	255.9	263.8



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